

**Amendments to the Specification:**

Please insert the following new paragraph after line 1 of page 1 (after the title)

CROSS REFERENCE TO CO-PENDING APPLICATION

The subject matter of the present application is a divisional of Application Serial No. 10/178,235, which is also assigned to the assignee of the present invention.

Please amend the paragraph on page 10 beginning at line 11, as follows:

Referring to FIG. 5 and FIG. 6, the FIG. 6 is schematic PMSCR with controlled N well guard ring structure 410 that is formed within the substrate 400. A first lightly doped well region 412 and a second lightly doped well region 414 are formed simultaneously within the substrate 400, wherein the first and second lightly doped well region 412, 414 having the second conductivity type such as N type. The embodiment of the present invention, the second lightly doped well region 414 is used as controlled N well guard ring to collect the electrons. In addition, a third lightly doped well region 416 of the first conductivity type is formed within the substrate 400 adjacent to the second lightly doped well region 414. Then, a first heavily doped region 430 of the second conductivity type is formed in the first lightly doped well region 412, and is electrically coupled to the first node 460, wherein the first node can be anode. Next, a second heavily doped region 432 of the second-first conductivity type is formed in the first lightly doped well region 412, and is electrically coupled to the first

node 460. Thereafter, the third heavily doped region 434 is formed in the third lightly doped well region 416, and is electrically coupled to the third node 490, wherein the third node 490 can be cathode. Then, a ~~forth~~fourth heavily doped region 436 of the first conductivity type is formed in the third lightly doped well region 416, and is electrically coupled to the third node 490.